

OUTLINE DRAWING

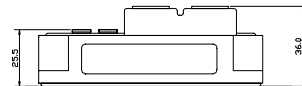
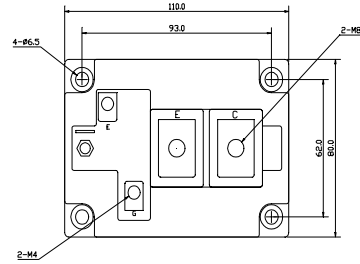
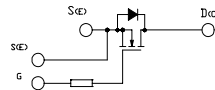
FEATURES

- * Trench Gate MOS FET Module
- * Super Low Rds(ON) 1.4 milliohms (@800A)
- * With Fast Recovery Source-Drain Diode

TYPICAL APPLICATIONS

- * Chopper Control For FORKLIFTS

Circuit



Approximate Weight : 650g

MAXMUM RATINGS

Ratings		Symbol	PHM8001		Unit
Drain-Source Voltage (V _{GS} =0V)		V _{DSS}	150		V
Gate - Source Voltage		V _{GSS}	+/- 20		V
Continuous Drain Current	Duty=50%	I _D	800 (T _c =25°C)		A
	D.C.		640 (T _c =25°C)		
Pulsed Drain Current		I _{DM}	1,600 T _c =25°C)		A
Total Power Dissipation		P _D	2,650 T _c =25°C)		W
Operating Junction Temperature Range		T _{jw}	-40 to +150		°C
Storage Temperature Range		T _{stg}	-40 to +125		°C
Isolation Voltage Terminals to Base AC, 1 min.)		V _{ISO}	2,500		V
Mounting Torque	Module Base to Heatsink	F _{TOR}	3.0		N•m
	Gate Terminals		M4	1.4	
	Bus Bar to Main Terminals		M8	10.5	

ELECTRICAL CHARACTERISTICS (@ $T_c=25^\circ C$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=V_{DSS}, V_{GS}=0V$	-	-	4.8	mA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	4.8	μA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=16mA$	1.0	2.0	3.2	V
Static Drain-Source On-Resistance	$r_{DS(on)}$	$V_{GS}=10V, I_D=800A$	-	1.15	1.4	m-ohm
Drain-Source On-Voltage	$V_{DS(on)}$	$V_{GS}=10V, I_D=800A$	-	1.10	1.25	V
Forward Transconductance	g_{fs}	$V_{DS}=15V, I_D=800A$	-	-	-	S
Input Capacitance	C_{ies}	$V_{DS}=10V, V_{GS}=0V, f=1MHz$	-	165	-	nF
Output Capacitance	C_{oss}		-	20	-	nF
Reverse Transfer Capacitance	C_{rss}		-	20	-	nF
Rise Time	t_r	$V_{DD}=80V$ $I_D=400A$ $V_{GS}=-5V, +10V$ $R_G=0.75\ ohm$	-	500	-	ns
Turn-On Delay Time	$t_{d(on)}$		-	880	-	
Fall Time	t_f		-	180	-	
Turn-Off Delay Time	$t_{d(off)}$		-	1,300	-	

FREE WHEELING DIODES RATINGS & CHARACTERISTICS ($T_c=25^\circ C$)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Continuous Source Current	I_S	Duty=50%.	-	-	800	A
		D.C. (Terminal Temperature=80 $^\circ C$)	-	-	650	
Pulsed Source Current	I_{SM}	-	-	-	1,600	A
Diode Forward Voltage	V_{SD}	$I_S=800A$	-	1.10	1.76	V
Reverse Recovery Time	t_{rr}	$I_S=800A, -dis/dt=1,600A/\mu s$	-	130	-	ns

THERMAL CHARACTERISTICS

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Thermal Resistance, Junction to Case	$R_{th(jc)}$		-	-	0.047	$^\circ C/W$
Thermal Resistance, Case to Heatsink	$R_{th(cf)}$	Mounting surface flat, smooth, and greased	-	-	0.035	

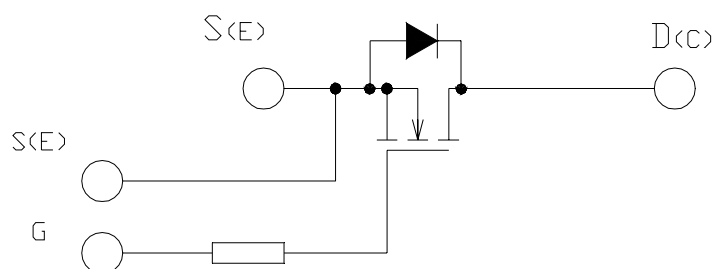
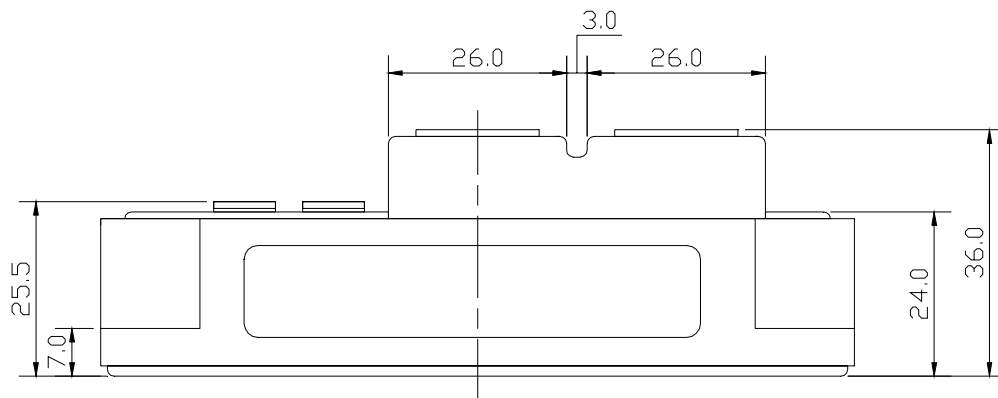
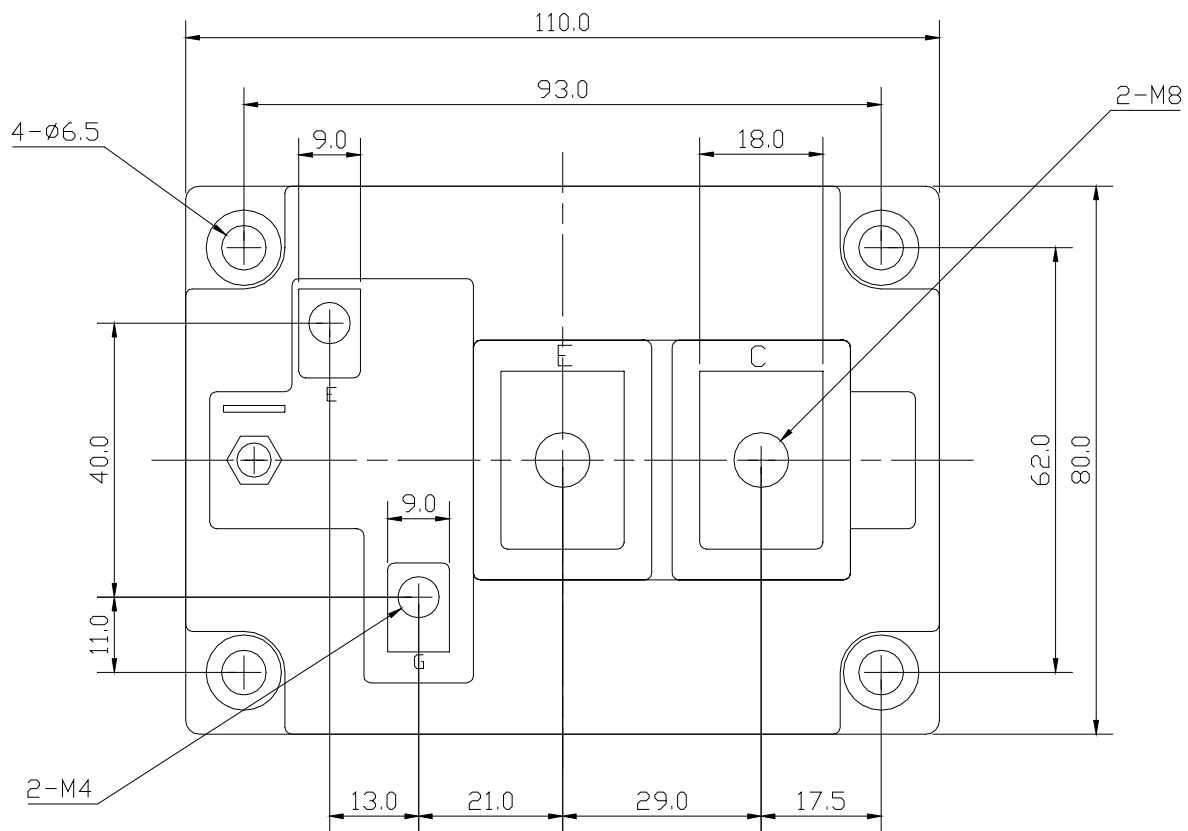


Fig.1- Output Characteristics (Typical)

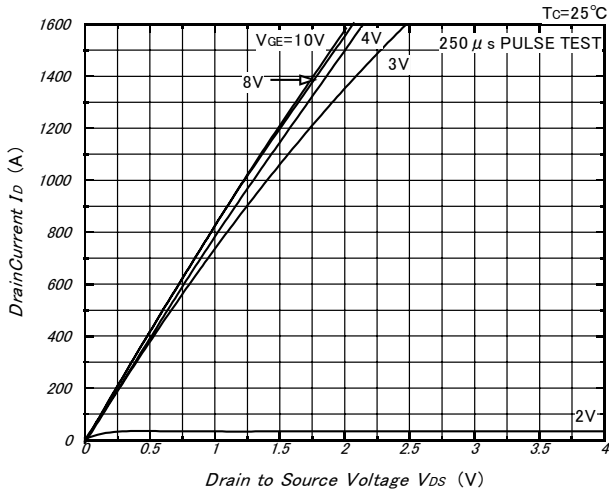


Fig.2- Drain to Source On Voltage vs. Gate to Source Voltage (Typical)

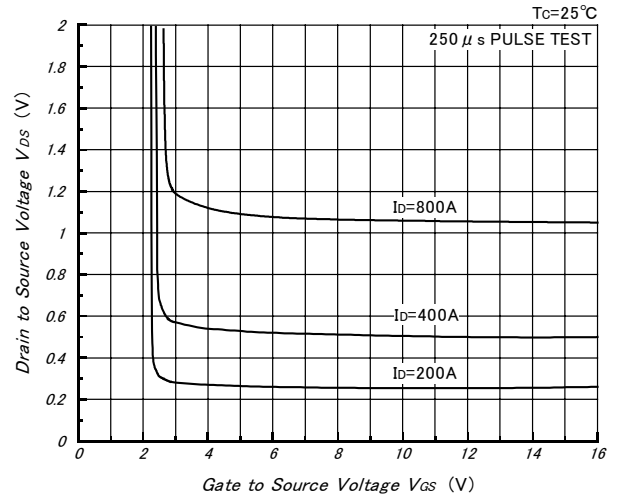


Fig.3- Drain to Source On Voltage vs. Junction Temperature (Typical)

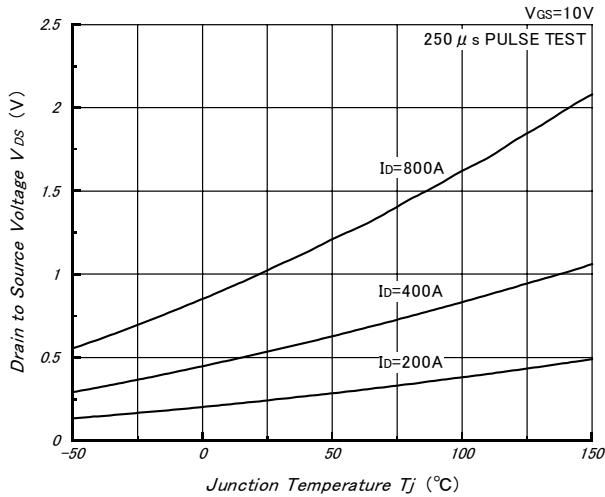


Fig.4- Capacitance vs. Drain to Source Voltage (Typical)

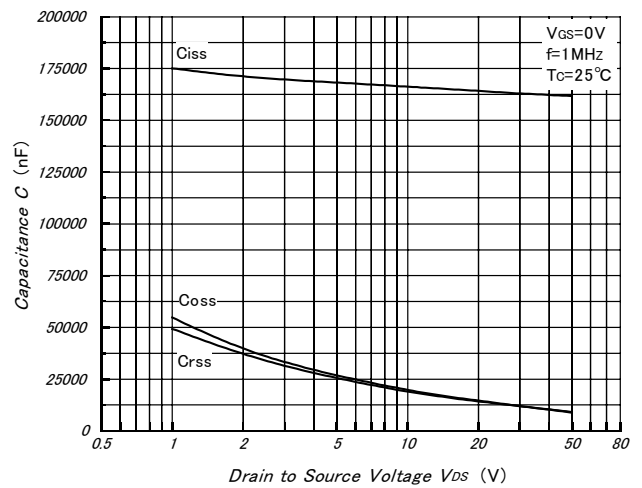


Fig.5- Gate Charge vs. Gate to Source Voltage (Typical)

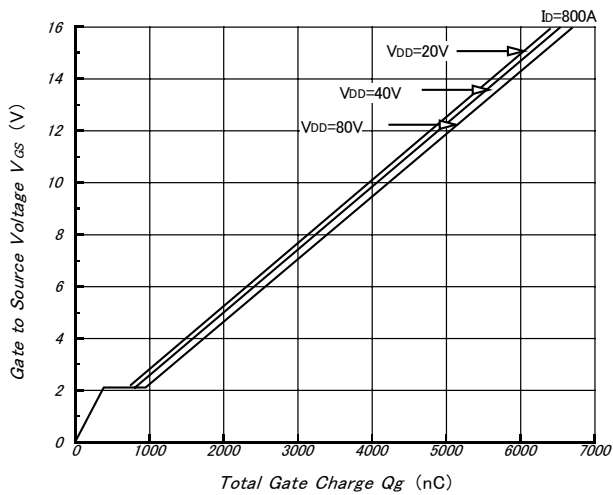


Fig.6- Series Gate Impedance vs. Switching Time (Typical)

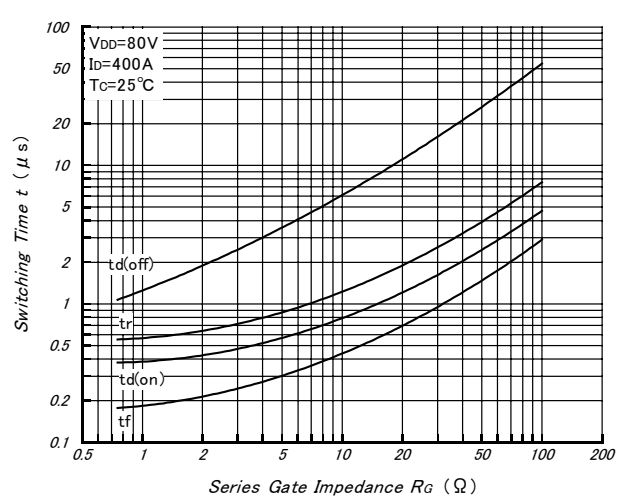


Fig.7- Drain Current vs. Switching Time (Typical)

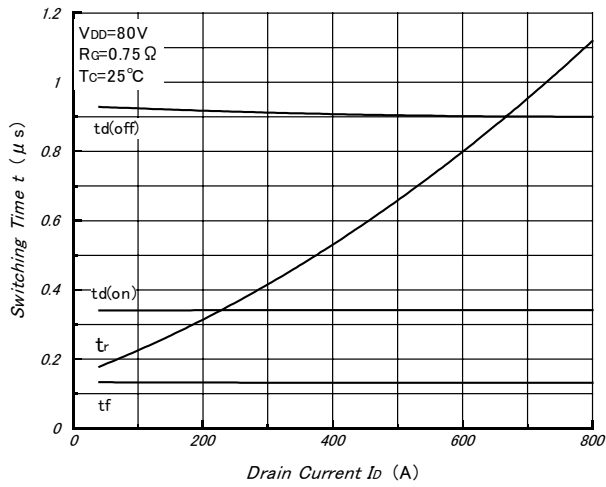


Fig.8- Source to Drain Diode Forward Characteristics (Typical)

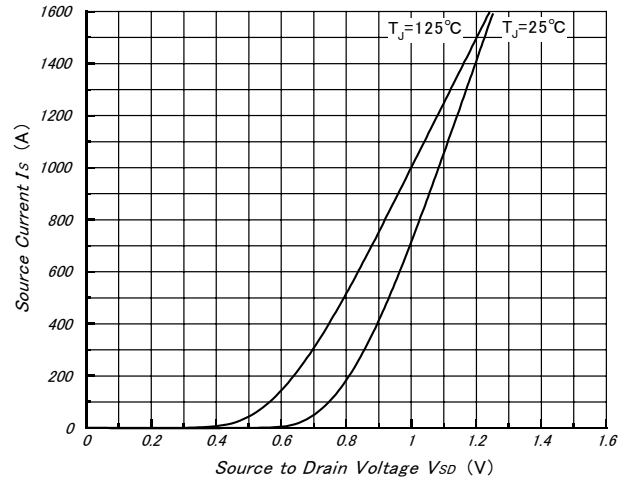


Fig.9- Reverse Recovery Characteristics (Typical)

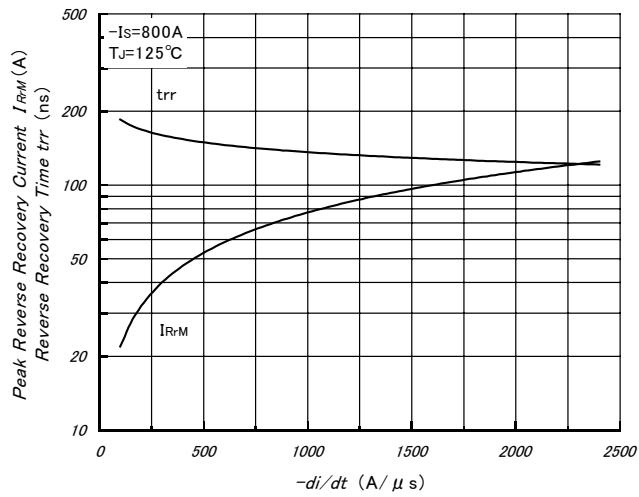


Fig.10- Maximum Transient Thermal Impedance

